

preliminary

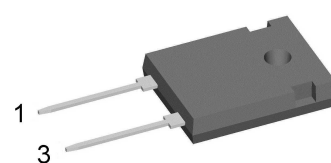
Sonic Fast Recovery Diode

V_{RRM}	=	600 V
I_{FAV}	=	30 A
t_{rr}	=	40 ns

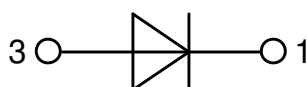
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DHG30I600HA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

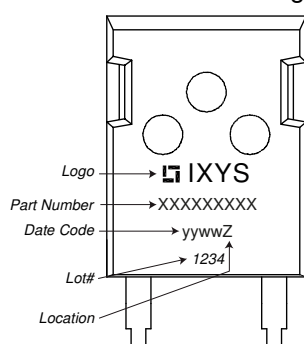
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			50	μA	
		V _R = 600 V	T _{VJ} = 125°C			4	mA	
V _F	forward voltage drop	I _F = 30 A	T _{VJ} = 25°C			2.26	V	
		I _F = 60 A				3.11	V	
		I _F = 30 A	T _{VJ} = 125°C			2.21	V	
		I _F = 60 A				3.17	V	
I _{FAV}	average forward current	T _C = 85°C rectangular d = 0.5	T _{VJ} = 150°C			30	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.17	V	
r _F	slope resistance					32	mΩ	
R _{thJC}	thermal resistance junction to case					0.7	K/W	
R _{thCH}	thermal resistance case to heatsink				0.3		K/W	
P _{tot}	total power dissipation	T _C = 25°C				180	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		200	A	
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C	16		pF	
I _{RM}	max. reverse recovery current	} I _F = 30 A; V _R = 300 V -di _F /dt = 600 A/μs		T _{VJ} = 25 °C	13		A	
				T _{VJ} = 125 °C	17		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	40		ns	
				T _{VJ} = 125 °C	60		ns	

preliminary

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			70	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 30 = Current Rating [A]
 I = Single Diode
 600 = Reverse Voltage [V]
 HA = TO-247AD (2)

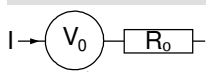
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG30I600HA	DHG30I600HA	Tube	30	503094

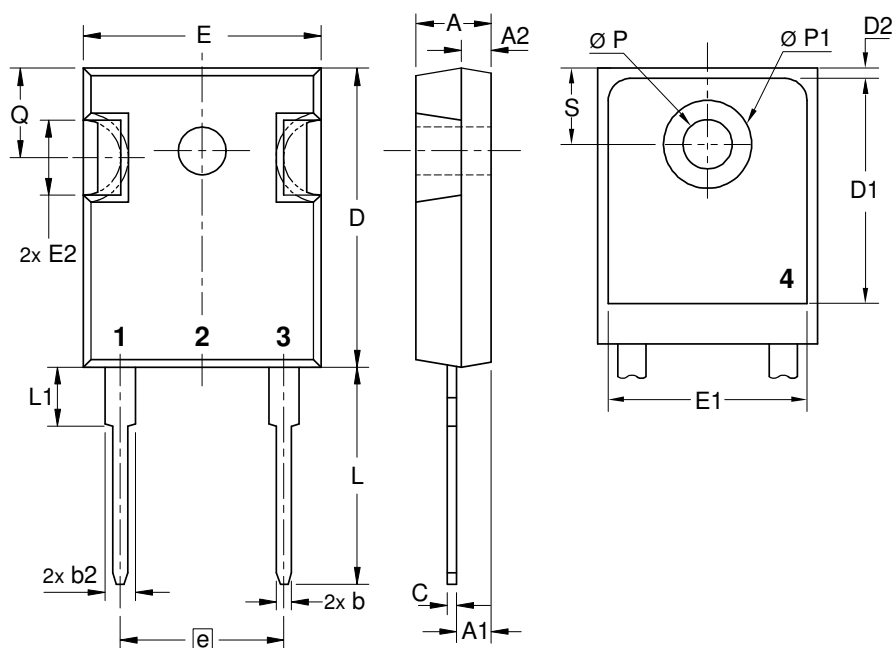
Similar Part	Package	Voltage class
DHG30I600PA	TO-220AC (2)	600
DHG30IM600PC	TO-263AB (D2Pak) (2)	600

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

		Fast Diode	
$V_{0\max}$	threshold voltage	1.17	V
$R_{0\max}$	slope resistance *	29	mΩ

Outlines TO-247


Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430	BSC	10.92	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



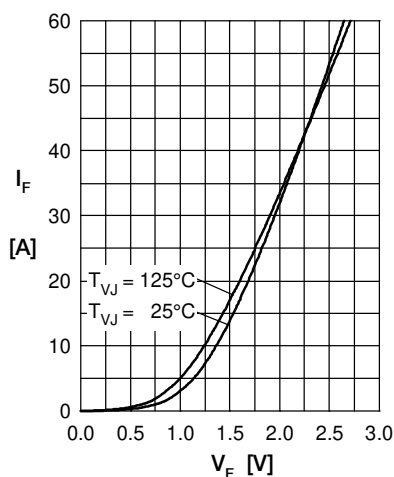
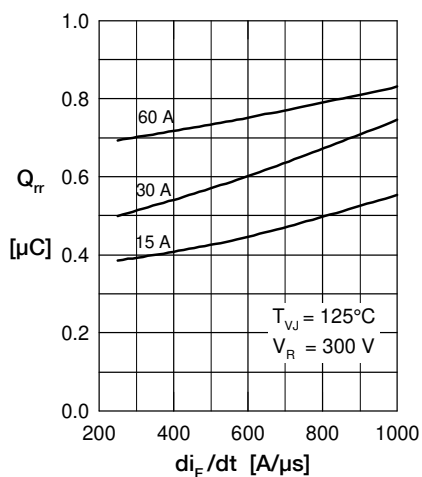
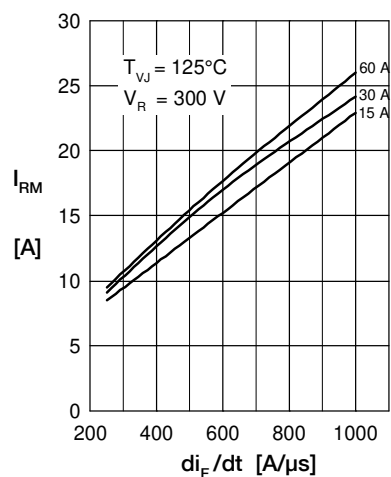
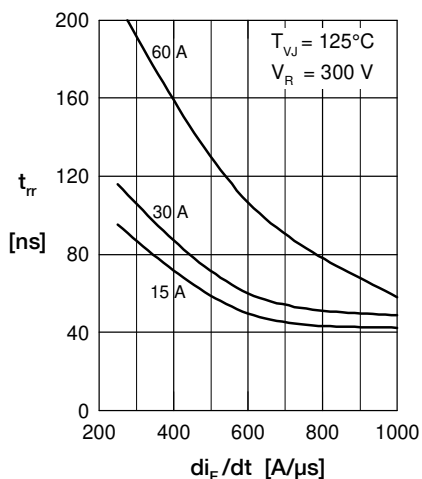
Fast Diode

 Fig. 1 Typ. Forward current versus V_F

 Fig. 2 Typ. reverse recov. charge Q_{rr} versus di_F/dt

 Fig. 3 Typ. peak reverse current I_{RM} versus di_F/dt

 Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

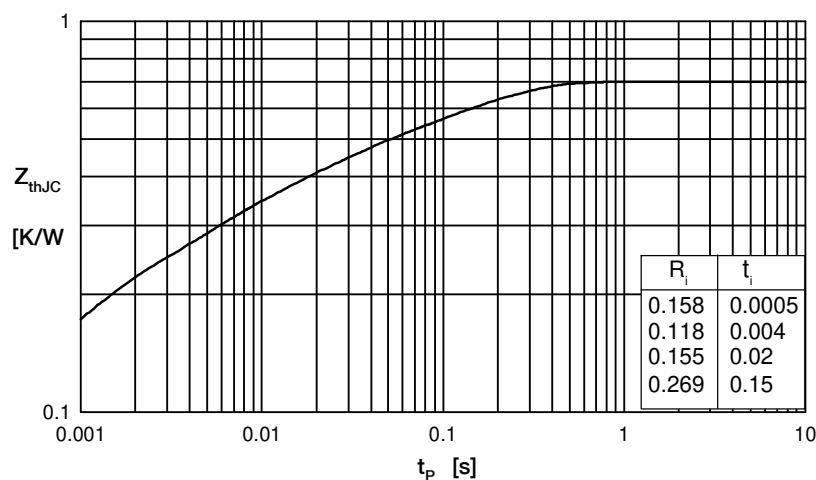
 Fig. 6 Typ. recovery energy E_{rec} versus di_F/dt


Fig. 7 Typ. transient thermal impedance junction to case